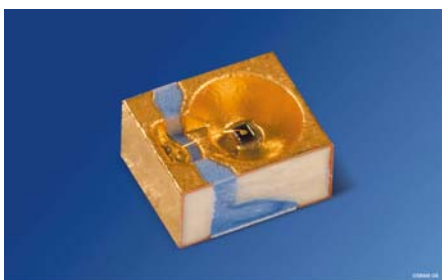
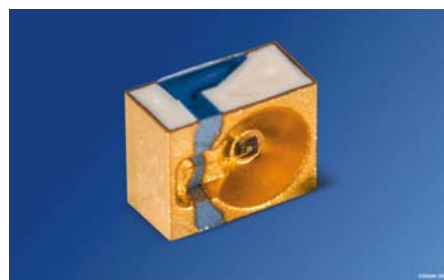


Engwinklige LED im MIDLED-Gehäuse
Narrow beam LED in MIDLED package
Lead (Pb) Free Product - RoHS Compliant

SFH 4600
SFH 4605



SFH 4600



SFH 4605

Nicht für Neuentwicklungen / Not for new designs

Wesentliche Merkmale

- Leistungsstarke GaAs-LED (35 mW) mit typischer Emissionswellenlänge 950 nm
- Enger Abstrahlwinkel ($\pm 20^\circ$)
- Geringe Bauhöhe
- Als Toplooker und Sidelooker einsetzbar
- SFH 4600: Gurtung als Toplooker
- SFH 4605: Gurtung als Sidelooker

Features

- High Power GaAs-LED (35 mW) with typical peak wavelength of 950 nm
- Narrow halfangle ($\pm 20^\circ$)
- Low profile component
- Usable as top-looking and side-looking device
- SFH 4600: Taping as Toplooker
- SFH 4605: Taping as Sidelooker

Anwendungen

- Lichtschranken, Lichtvorhänge
- Sensorik
- IR Scheinwerfer

Applications

- Interrupters, Lightcurtains
- Sensors
- IR floodlight

Sicherheitshinweise

Je nach Betriebsart emittieren diese Bauteile hochkonzentrierte, nicht sichtbare Infrarot-Strahlung, die gefährlich für das menschliche Auge sein kann. Produkte, die diese Bauteile enthalten, müssen gemäß den Sicherheitsrichtlinien der IEC-Normen 60825-1 und 62471 behandelt werden.

Safety Advices

Depending on the mode of operation, these devices emit highly concentrated non visible infrared light which can be hazardous to the human eye. Products which incorporate these devices have to follow the safety precautions given in IEC 60825-1 and IEC 62471.

Typ Type	Bestellnummer Ordering Code	Strahlstärkegruppierung ¹⁾ ($I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$) Radiant Intensity Grouping ¹⁾ I_e (mW/sr)
SFH 4600	Q65110A1575	≥ 16 (typ. 30)
SFH 4605	Q65110A1576	≥ 16 (typ. 30)

¹⁾ gemessen bei einem Raumwinkel $\Omega = 0.01 \text{ sr}$ / measured at a solid angle of $\Omega = 0.01 \text{ sr}$



ATTENTION - Observe Precautions For Handling - Electrostatic Sensitive Device

Grenzwerte Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	T_{op}, T_{stg}	- 40 ... + 100	°C
Sperrspannung Reverse voltage	V_R	5	V
Vorwärtsgleichstrom, $T_A \leq 60$ °C Forward current	I_F	100	mA
Stoßstrom, $t_p = 300$ µs, $D = 0$, $T_A \leq 60$ °C Surge current	I_{FSM}	1	A
Verlustleistung $T_A = 25$ °C Power dissipation	P_{tot}	180	mW
Wärmewiderstand Sperrschicht - Umgebung bei Montage auf FR4 Platine, Padgröße je 16 mm ² Thermal resistance junction - ambient mounted on PC-board (FR4), pads size 16 mm ² each	R_{thJA}	340	K/W
Wärmewiderstand Sperrschicht - Lötstelle bei Montage auf Metall-Block Thermal resistance junction - soldering point, mounted on metal block	R_{thJS}	180	K/W

Kennwerte ($T_A = 25$ °C)

Characteristics

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der Strahlung Wavelength at peak emission $I_F = 100$ mA	λ_{peak}	950	nm
Spektrale Bandbreite bei 50% von I_{max} Spectral bandwidth at 50% of I_{max} $I_F = 100$ mA	$\Delta\lambda$	40	nm

Kennwerte ($T_A = 25\text{ °C}$)
Characteristics (cont'd)

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Abstrahlwinkel Half angle	φ	± 20	Grad deg.
Aktive Chipfläche Active chip area	A	0.09	mm ²
Abmessungen der aktiven Chipfläche Dimension of the active chip area	$L \times B$ $L \times W$	0.3×0.3	mm ²
Schaltzeiten, I_e von 10% auf 90% und von 90% auf 10%, bei $I_F = 100\text{ mA}$, $R_L = 50\ \Omega$ Switching times, I_e from 10% to 90% and from 90% to 10%, $I_F = 100\text{ mA}$, $R_L = 50\ \Omega$	t_r, t_f	10	ns
Durchlassspannung Forward voltage $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$ $I_F = 1\text{ A}$, $t_p = 100\ \mu\text{s}$	V_F V_F	1.5 (< 1.8) 3.2 (< 4.3)	V V
Sperrstrom Reverse current $V_R = 5\text{ V}$	I_R	not designed for reverse operation	μA
Gesamtstrahlungsfluss Total radiant flux $I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	$\Phi_{e\text{ typ}}$	35	mW
Temperaturkoeffizient von I_e bzw. Φ_e , $I_F = 100\text{ mA}$ Temperature coefficient of I_e or Φ_e , $I_F = 100\text{ mA}$	TC_I	- 0.44	%/K
Temperaturkoeffizient von V_F , $I_F = 100\text{ mA}$ Temperature coefficient of V_F , $I_F = 100\text{ mA}$	TC_V	- 1.5	mV/K
Temperaturkoeffizient von λ , $I_F = 100\text{ mA}$ Temperature coefficient of λ , $I_F = 100\text{ mA}$	TC_λ	+ 0.2	nm/K

Strahlstärke I_e in Achsrichtung¹⁾

gemessen bei einem Raumwinkel $\Omega = 0.01$ sr

Radiant Intensity I_e in Axial Direction

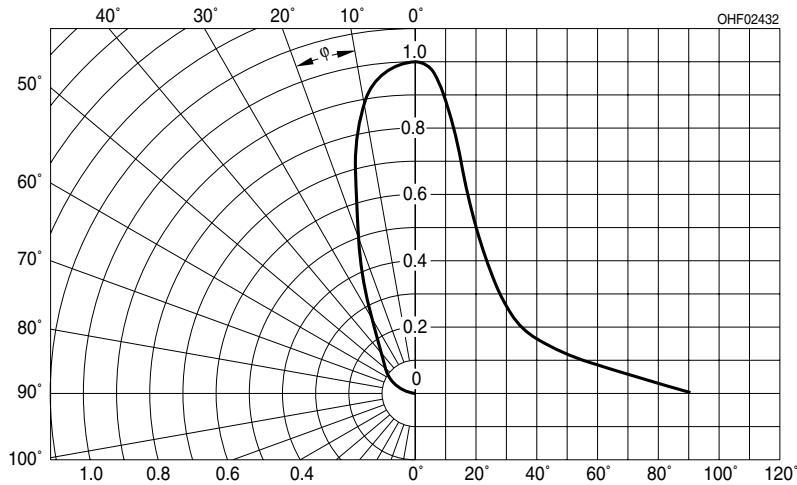
at a solid angle of $\Omega = 0.01$ sr

Bezeichnung Parameter	Symbol	Werte Values			Einheit Unit
		-S	-T	-U	
Strahlstärke Radiant intensity $I_F = 100$ mA, $t_p = 20$ ms	$I_{e \text{ min}}$ $I_{e \text{ max}}$	16 32	25 50	40 80	mW/sr mW/sr
Strahlstärke Radiant intensity $I_F = 1$ A, $t_p = 100$ μ s	$I_{e \text{ typ}}$	160	220	280	mW/sr

¹⁾ Nur eine Gruppe in einer Verpackungseinheit (Streuung kleiner 2:1) /
Only one group in one packing unit (variation lower 2:1)

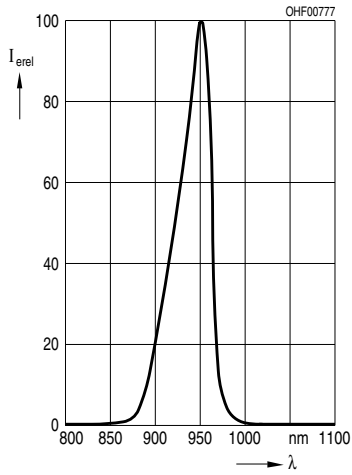
Abstrahlcharakteristik

Radiation Characteristics $I_{rel} = f(\varphi)$



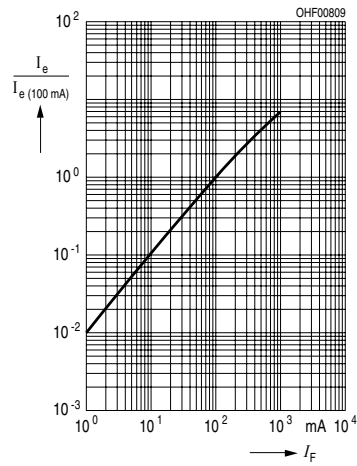
Relative Spectral Emission

$I_{rel} = f(\lambda)$



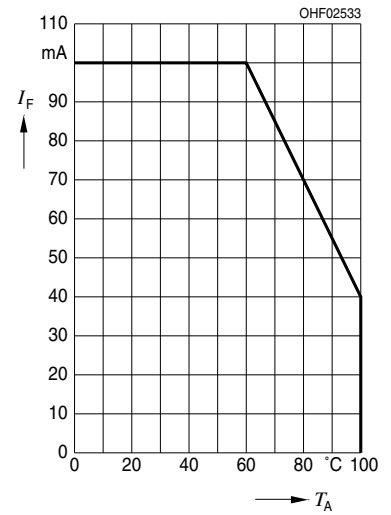
Radiant Intensity $\frac{I_e}{I_e 100 \text{ mA}} = f(I_F)$

Single pulse, $t_p = 20 \mu\text{s}$



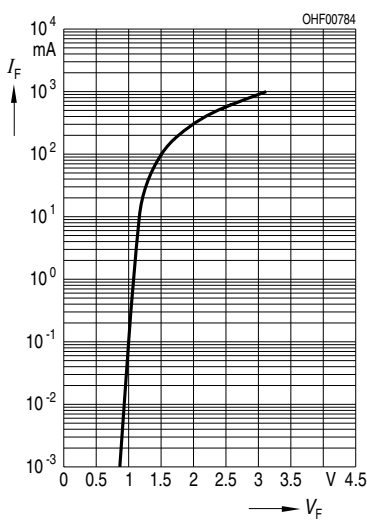
Max. Permissible Forward Current

$I_F = f(T_A), R_{thJA} = 340 \text{ K/W}$



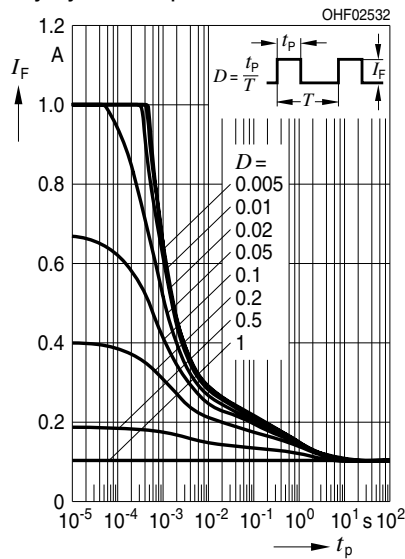
Forward Current $I_F = f(V_F)$

Single pulse, $t_p = 20 \mu\text{s}$

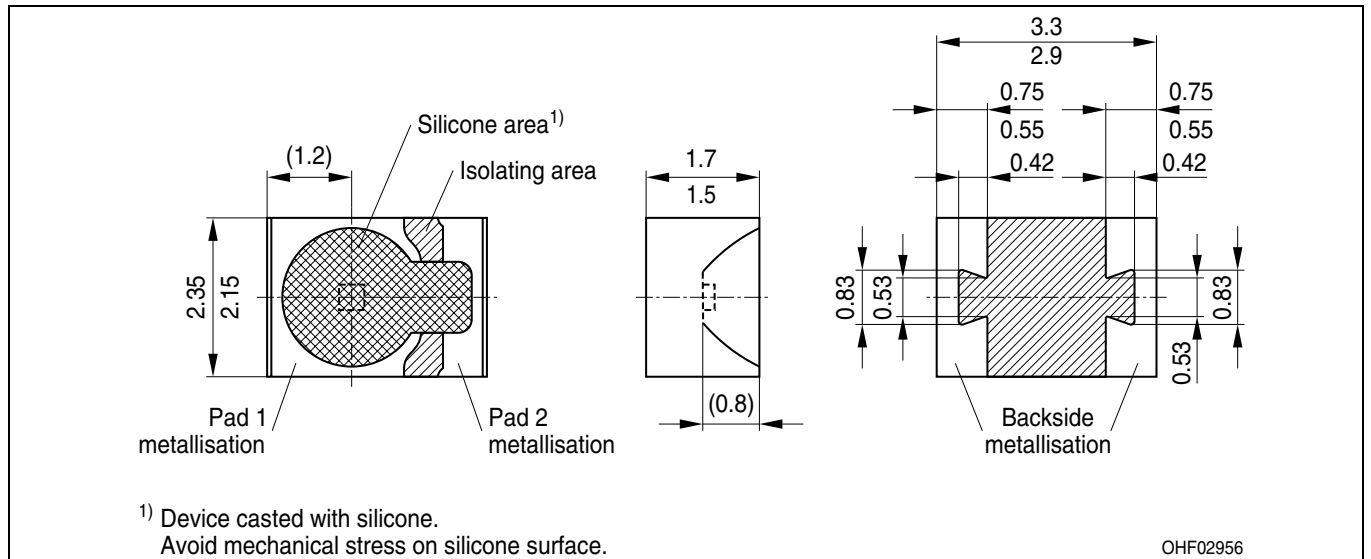


Permissible Pulse Handling Capability

$I_F = f(\tau), T_A \leq 60^\circ\text{C}$,
duty cycle $D = \text{parameter}$



**Maßzeichnung
Package Outlines**



Maße in mm / Dimensions in mm.

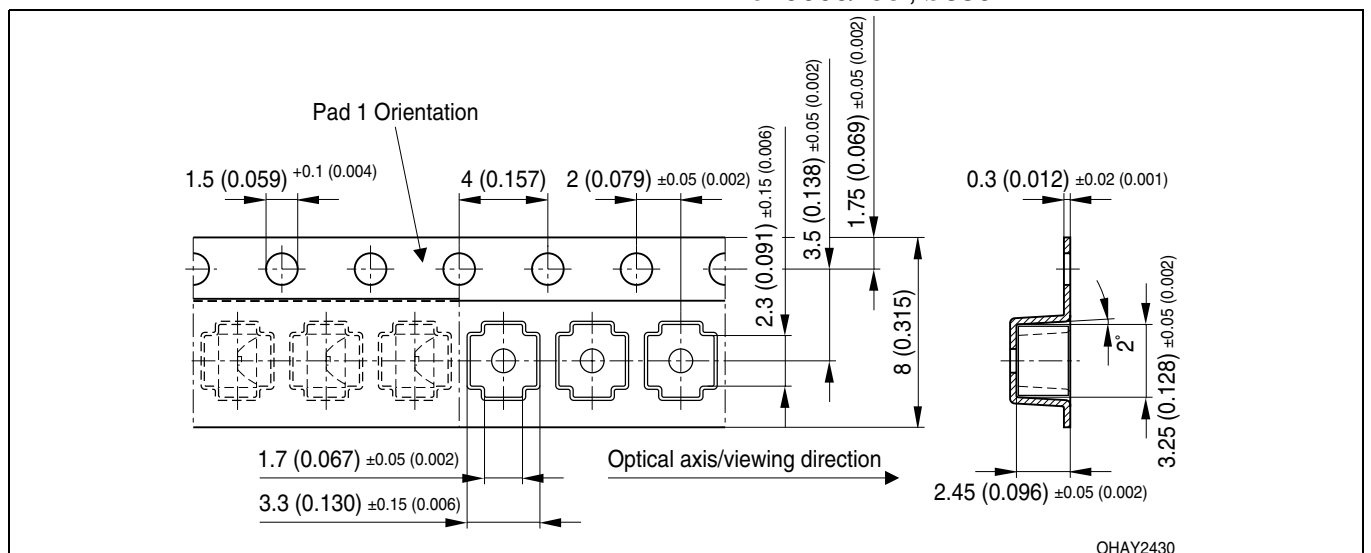
Gehäuse / Package	MID mit klarem Silikonverguss / MID casted with clear Silicone
Anschlussbelegung Pin configuration	Pad 1 = Anode / anode Pad 2 = Kathode / cathode

Gurtung / Polarität und Lage

Verpackungseinheit 2000/Rolle, ø180 mm
oder 9000/Rolle, ø330 mm

Method of Taping / Polarity and Orientation

Packing unit 2000/reel, ø180 mm
or 9000/reel, ø330 mm




Maße in mm (inch) / Dimensions in mm (inch).

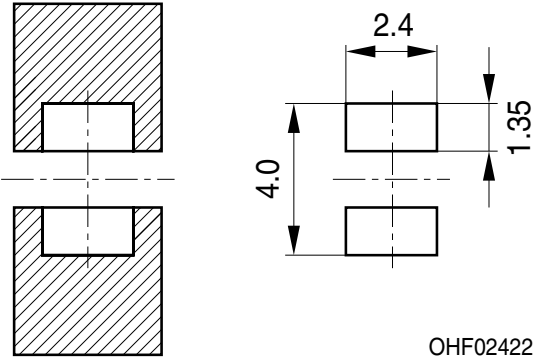
Empfohlenes Lötpaddesign
Recommended Solder Pad Design

SFH 4600

Padgeometrie für verbesserte Wärmeableitung
 Pad design for improved heat dissipation

Cu-Fläche > 16 mm²
 Cu-area

 Lötstopplack
 Solder resist




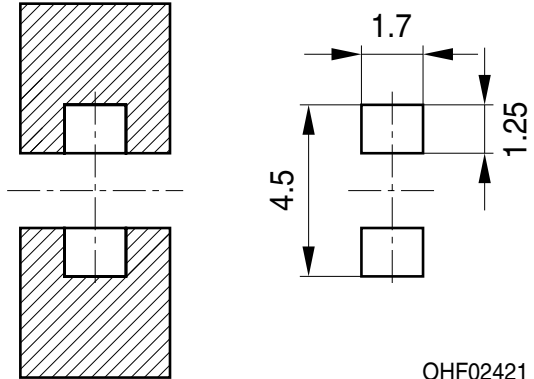
OHF02422

SFH 4605

Padgeometrie für verbesserte Wärmeableitung
 Pad design for improved heat dissipation

Cu-Fläche > 16 mm²
 Cu-area

 Lötstopplack
 Solder resist



OHF02421

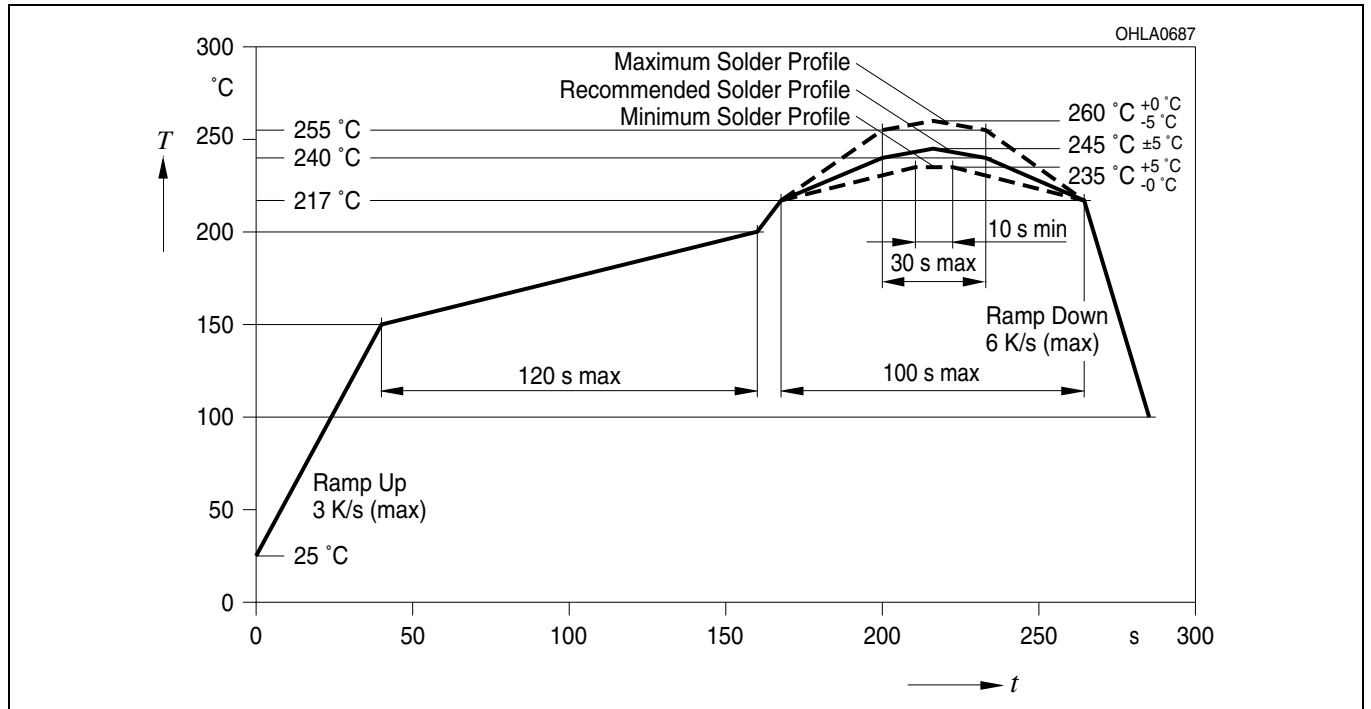
Maße in mm / Dimensions in mm.

Verarbeitungshinweis: Das Gehäuse ist mit Silikon vergossen. Mechanischer Stress auf der Bauteiloberfläche sollte so gering wie möglich gehalten werden.

Handling indication: The package is casted with silicone. Mechanical stress at the surface of the unit should be as low as possible.

Lötbedingungen
Soldering Conditions
Reflow Lötprofil für bleifreies Löten
Reflow Soldering Profile for lead free soldering

Vorbehandlung nach JEDEC Level 2
 Preconditioning acc. to JEDEC Level 2
 (nach J-STD-020C)
 (acc. to J-STD-020C)



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 Wernerwerkstrasse 2, D-93049 Regensburg
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¹ A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

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